

NVMFD5853N, NVMFD5853NWF

Power MOSFET

40 V, 10 mΩ, 53 A, Dual N-Channel, Dual SO-8FL

Features

- Small Footprint (5x6 mm) for Compact Designs
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- NVMFD5853NWF – Wettable Flanks Product
- AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free and Halogen-Free Device

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	40	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3)	Steady State	$T_C = 25^{\circ}\text{C}$	I_D	53	A
		$T_C = 100^{\circ}\text{C}$		37	
Power Dissipation $R_{\theta JC}$ (Notes 1, 2)		$T_C = 25^{\circ}\text{C}$	P_D	58	W
		$T_C = 100^{\circ}\text{C}$		29	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2 & 3)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	12	A
		$T_A = 100^{\circ}\text{C}$		8.7	
Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)		$T_A = 25^{\circ}\text{C}$	P_D	3.1	W
		$T_A = 100^{\circ}\text{C}$		1.6	
Pulsed Drain Current	$T_A = 25^{\circ}\text{C}$, $t_p = 10\text{ }\mu\text{s}$		I_{DM}	165	A
Operating Junction and Storage Temperature			T_J , T_{stg}	-55 to 175	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	53	A
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^{\circ}\text{C}$, $I_{L(pk)} = 28.3\text{ A}$, $L = 0.1\text{ mH}$)			E_{AS}	40	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 2)	$R_{\theta JC}$	2.6	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	48	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Continuous DC current rating. Maximum current for pulses as long as 1 second are higher but are dependent on pulse duration and duty cycle.

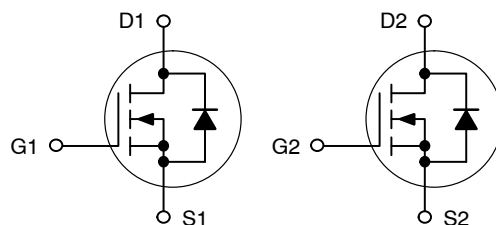


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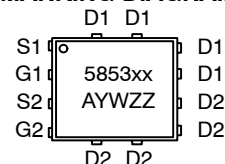
$V_{(BR)DSS}$	$R_{DS(on)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	10 mΩ @ 10 V	53 A

Dual N-Channel



DFN8 5x6
(SO8FL)
CASE 506BT

MARKING DIAGRAM



5853N = NVMFD5853N
5853WF = NVMFD5853NWF
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NVMFD5853NT1G	DFN8 (Pb-Free)	1500 / Tape & Reel
NVMFD5853NWF1G	DFN8 (Pb-Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			41.5		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	2.0		4.0	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-7.2		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		8.4	10	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 15\text{ A}$		44		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 25\text{ V}$		1225		pF
Output Capacitance	C_{oss}			150		
Reverse Transfer Capacitance	C_{rss}			100		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 32\text{ V}, I_D = 15\text{ A}$		24		nC
Threshold Gate Charge	$Q_{G(TH)}$			1.5		
Gate-to-Source Charge	Q_{GS}			5.2		
Gate-to-Drain Charge	Q_{GD}			6.6		
Plateau Voltage	V_{GP}			4.1		V

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}, I_D = 15\text{ A}, R_G = 2.5\text{ }\Omega$		9		ns
Rise Time	t_r			20		
Turn-Off Delay Time	$t_{d(off)}$			21		
Fall Time	t_f			3		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 15\text{ A}$	$T_J = 25^\circ\text{C}$		0.82	1.1	V
			$T_J = 125^\circ\text{C}$		0.72		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 15\text{ A}$		16		ns	
Charge Time	t_a			10			
Discharge Time	t_b			6			
Reverse Recovery Charge	Q_{RR}			9		nC	

4. Pulse Test: pulse width = 300 μs , duty cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

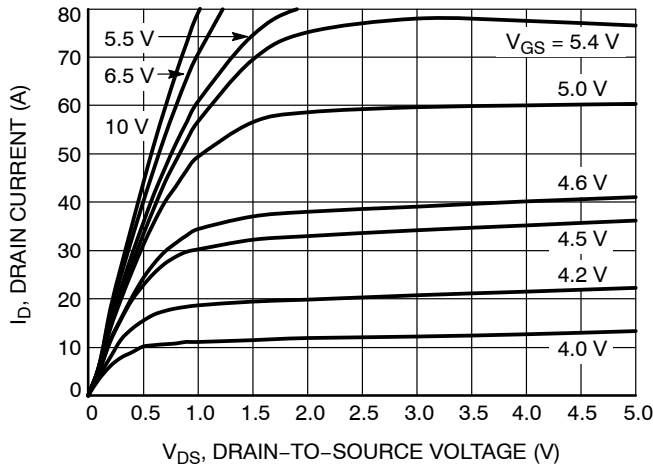


Figure 1. On-Region Characteristics

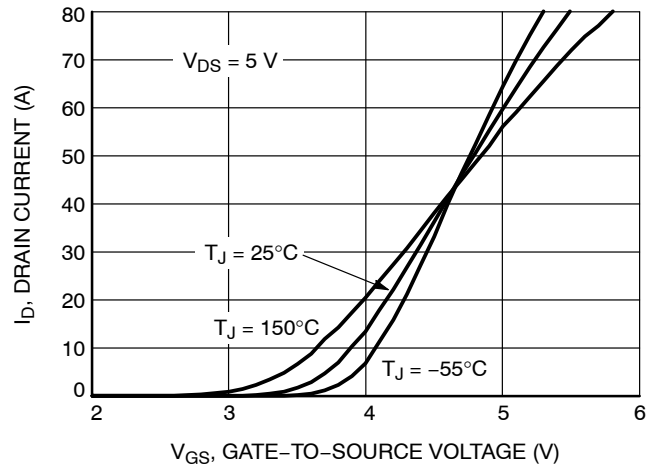


Figure 2. Transfer Characteristics

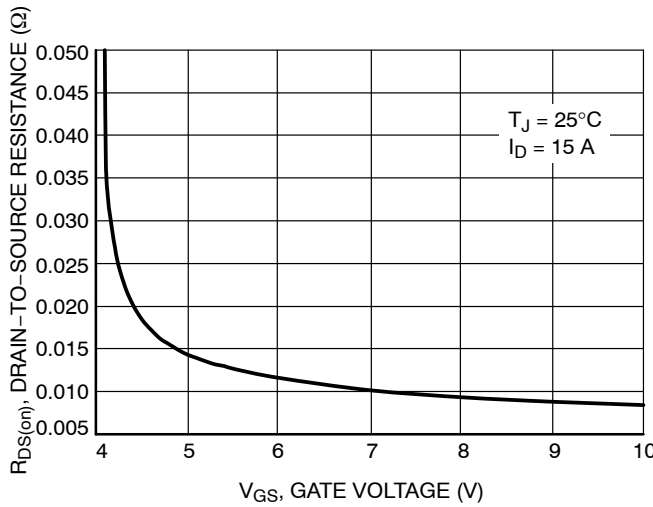


Figure 3. On-Resistance vs. Gate-to-Source Voltage

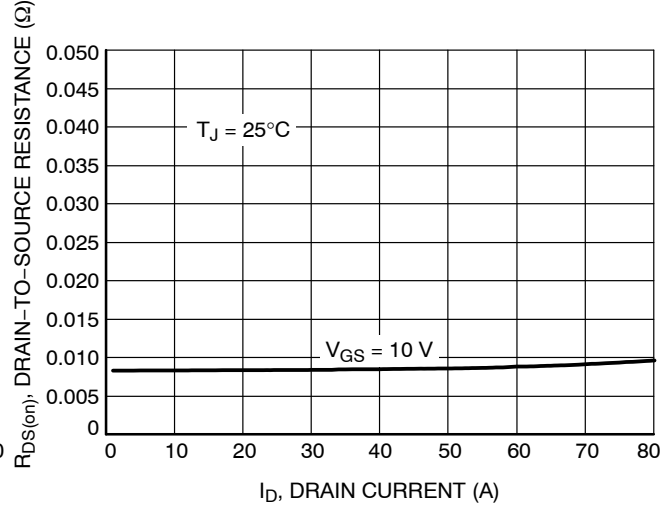


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

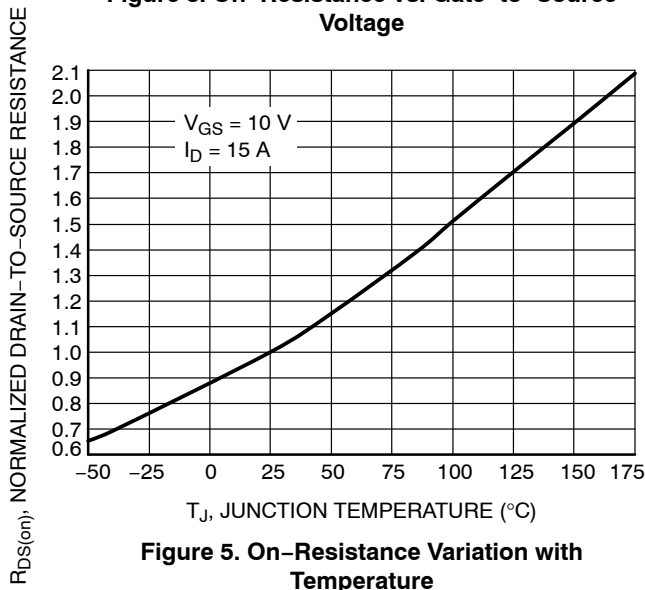


Figure 5. On-Resistance Variation with Temperature

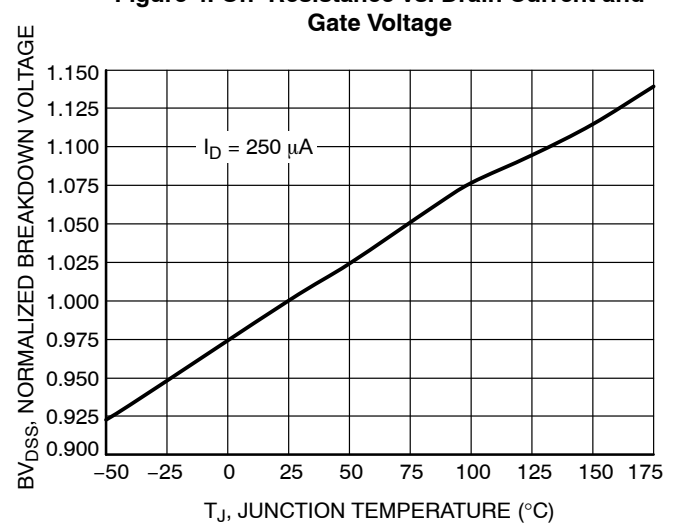


Figure 6. Breakdown Voltage Variation with Temperature

TYPICAL CHARACTERISTICS

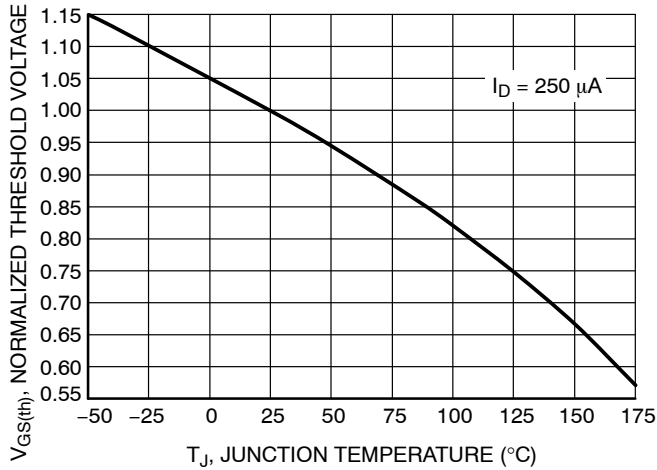


Figure 7. Threshold Voltage Variation with Temperature

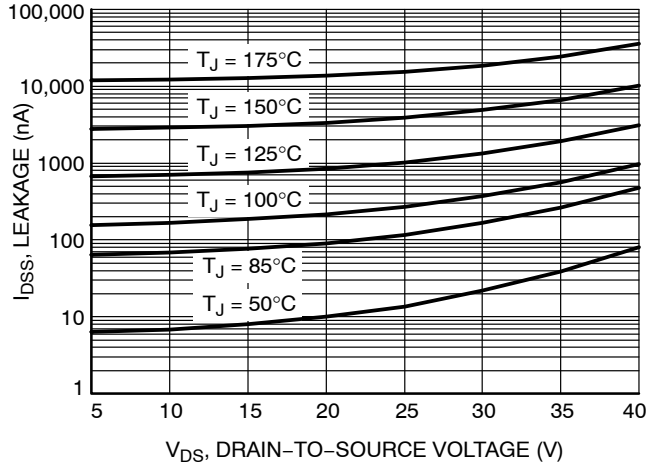


Figure 8. Drain-to-Source Leakage Current vs. Voltage

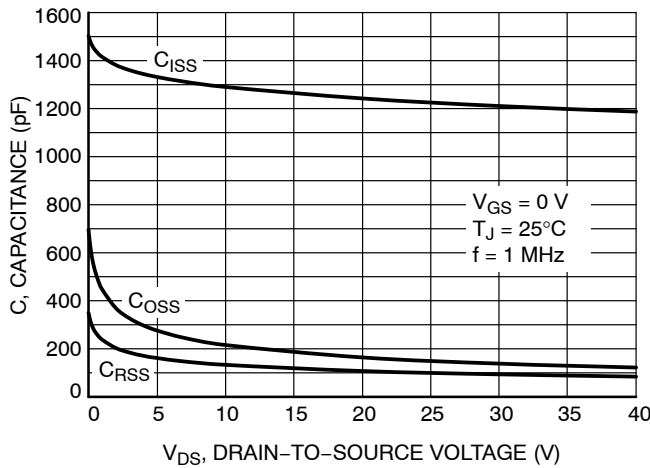


Figure 9. Capacitance Variation

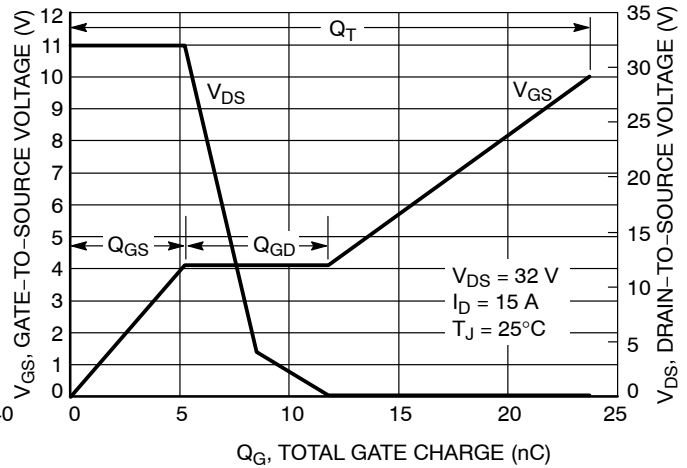


Figure 10. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

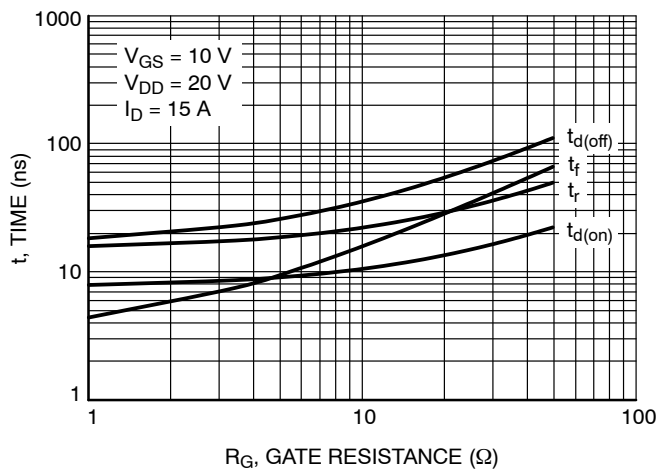


Figure 11. Resistive Switching Time Variation vs. Gate Resistance

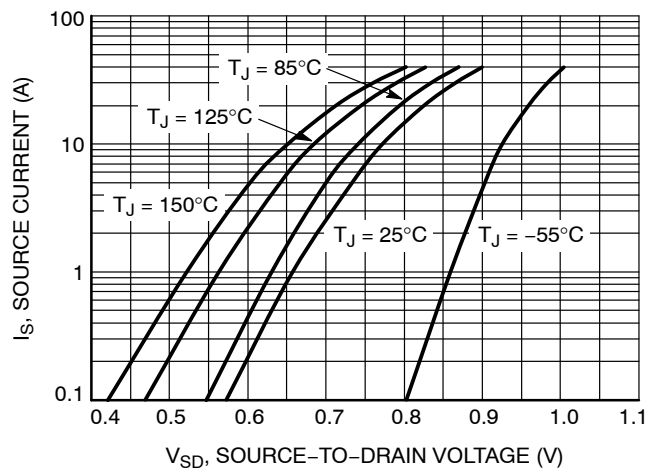


Figure 12. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS

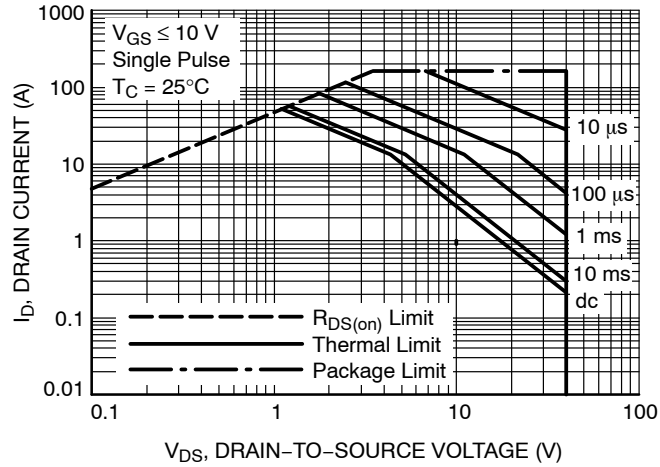


Figure 13. Maximum Rated Forward Biased Safe Operating Area

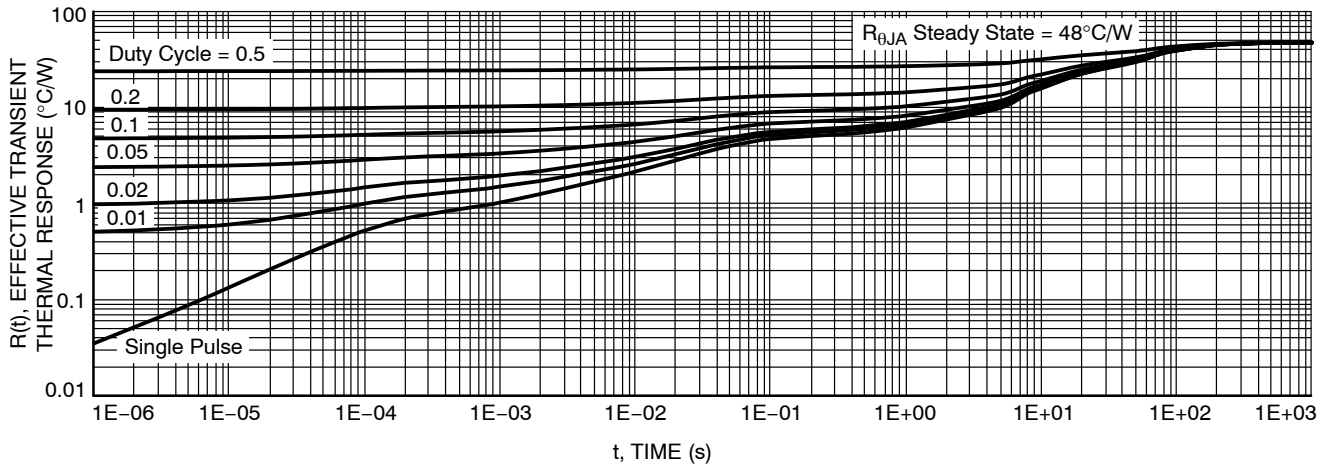


Figure 14. Thermal Impedance (Junction-to-Ambient)

AMEYA360

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